AMENDMENTS TO THE SPECIFICATION

Please replace the title with the following amended title:

~~METHOD OF MAKING~~ VERTICAL DIODE STRUCTURES

Please replace paragraph [001] with the following amended paragraph:

[001] This application is a continuation of Application No. 10/104,240, filed March 22, 2002, now U.S. Patent No. 6,784,046, which is a divisional of Application No. 09/505,953, filed on February 16, 2000, now U.S. Patent No. 6,750,091, which is a divisional of Application No. 09/150,317, filed on September 9, 1998, now U.S. Patent No. 6,194,746, which is a divisional of Application No. 08/932,791, filed on September 5, 1997, now U.S. Patent No. 5,854,102, which is a continuation of Application No. 08/609,505, filed on March 1, 1996, now abandoned, all of the foregoing being incorporated herein by reference.

Please add the following new paragraph after paragraph [085] and before paragraph [086]:

-- As is well known in the art, chalcogenides are materials that may be electrically stimulated to change states and resistivities, from an amorphous state to a crystalline state, for example, or to exhibit different resistivities while in a crystalline state. A chalcogenide material may be predictably placed in a particular resistivity state by, for example, running a current of a certain amperage through it. The resistivity state so fixed will remain unchanged unless and until a current having a different amperage within the programming range is run through the chalcogenide material.--